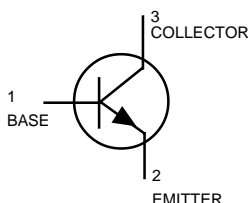
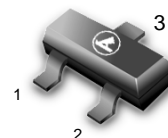


VHF/UHF Transistors

NPN Silicon


MMBTH10LT1

 CASE 318-08, STYLE 6
SOT-23 (TO-236AB)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	25	Vdc
Collector–Base Voltage	V_{CBO}	30	Vdc
Emitter–Base Voltage	V_{EBO}	3.0	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBTH10LT1 = 3EM

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	25	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 25\text{Vdc}, I_E = 0$)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 2.0\text{Vdc}, I_C = 0$)	I_{EBO}	—	—	100	nAdc

 1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.

 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

MMBTH10LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
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DC CHARACTERISTICS

DC Current Gain ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	60	—	—	—
Collector–Emitter Saturation Voltage ($I_C = 4.0\text{ mA}$, $I_B = 0.4\text{ mA}$)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base–Emitter On Voltage ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	V_{BE}	—	—	0.95	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current Gain–Bandwidth Product ($V_{CE} = 10\text{ Vdc}$, $I_C = 4.0\text{ mA}$, $f = 100\text{ MHz}$)	f_T	650	—	—	MHz
Collector –Base Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{cb}	—	—	0.7	pF
Collector –Base Feedback Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{fb}	—	—	0.65	pF
Collector Base Time Constant ($I_C = 4.0\text{ mA}$, $V_{CB} = 10\text{ Vdc}$, $f = 31.8\text{ MHz}$)	$r_b' C_C$	—	—	9.0	ps

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TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mAdc}$, $T_A = 25^\circ\text{C}$)

y_{ib} , INPUT ADMITTANCE

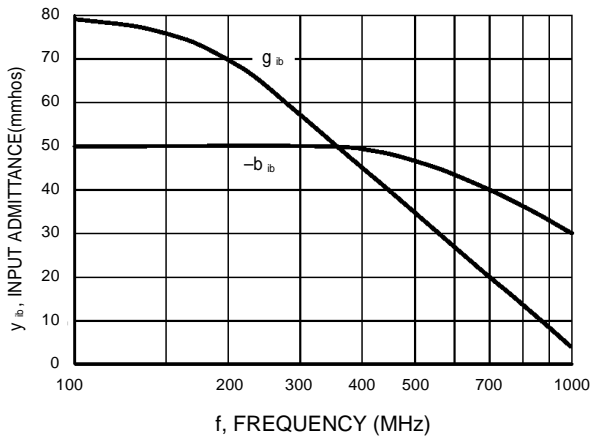


Figure 1. Rectangular Form

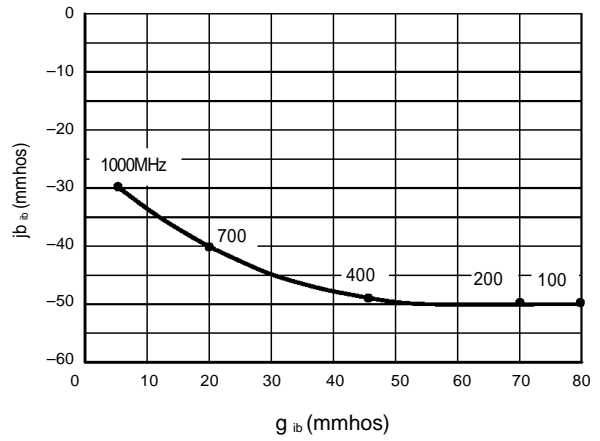


Figure 2. Polar Form

y_{fb} , FORWARD TRANSFER ADMITTANCE

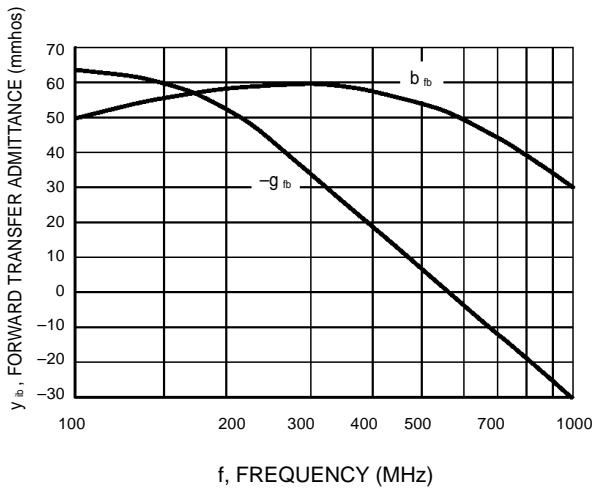


Figure 3. Rectangular Form

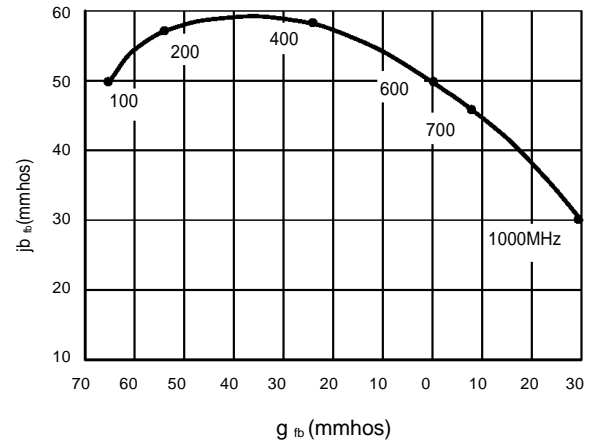


Figure 4. Polar Form

MMBTH10LT1

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10$ Vdc, $I_C = 4.0$ mAdc, $T_A = 25^\circ\text{C}$)

y_{rb} , REVERSE TRANSFER ADMITTANCE

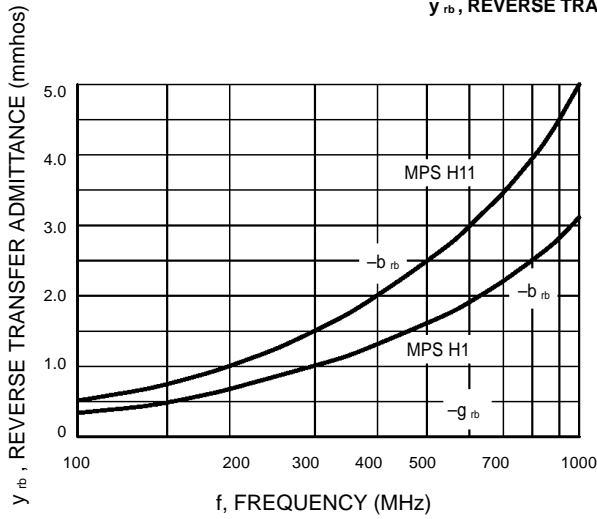


Figure 5. Rectangular Form

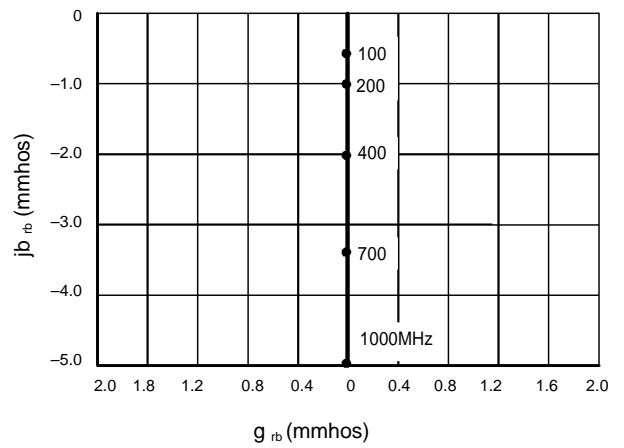


Figure 6. Polar Form

y_{ob} , OUTPUT ADMITTANCE

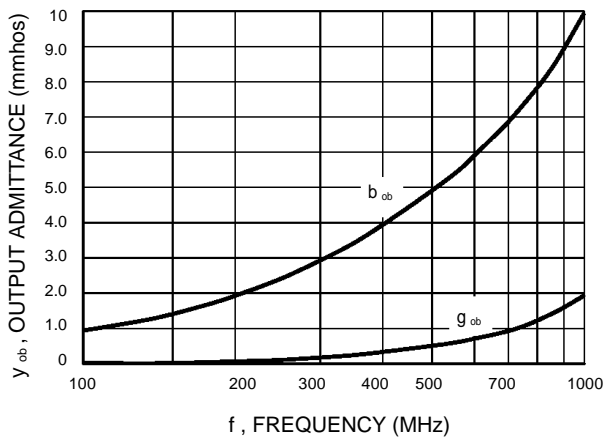


Figure 7. Rectangular Form

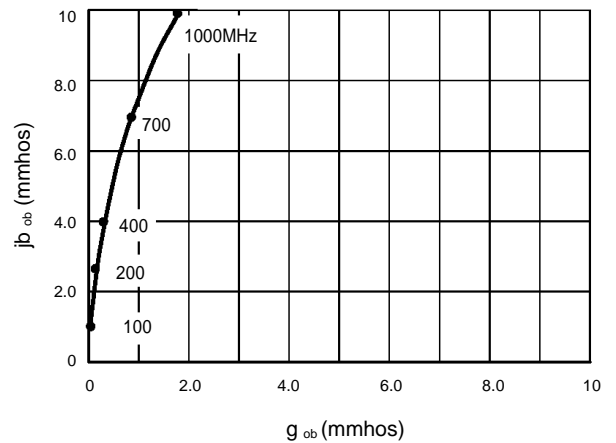


Figure 8. Polar Form